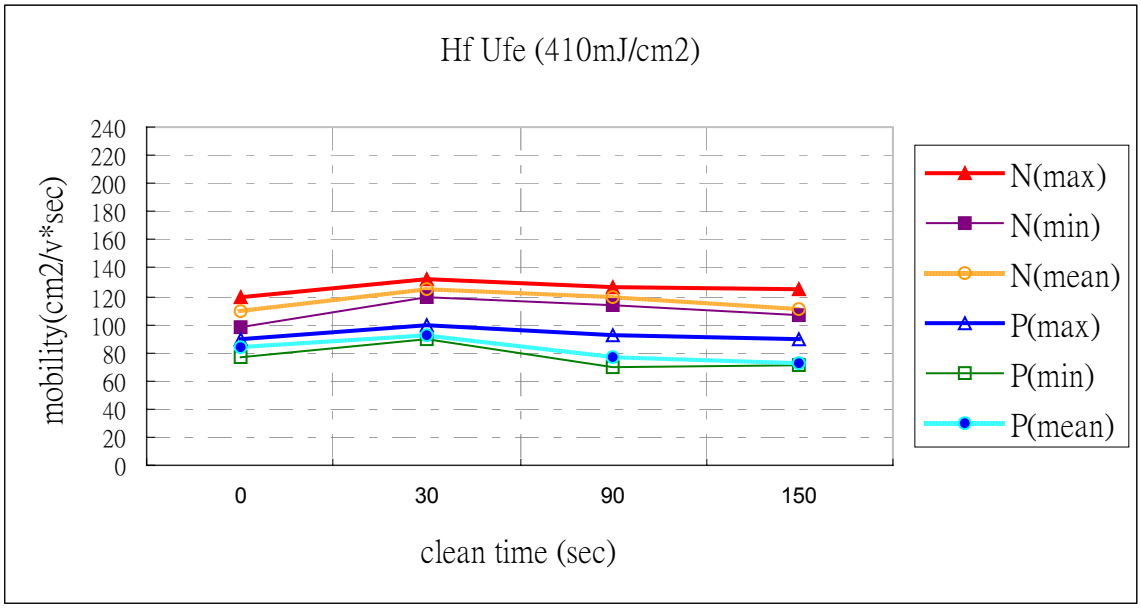

Fig. 2-52 The mobility of base pre treatment clean of HF1% in different clean time

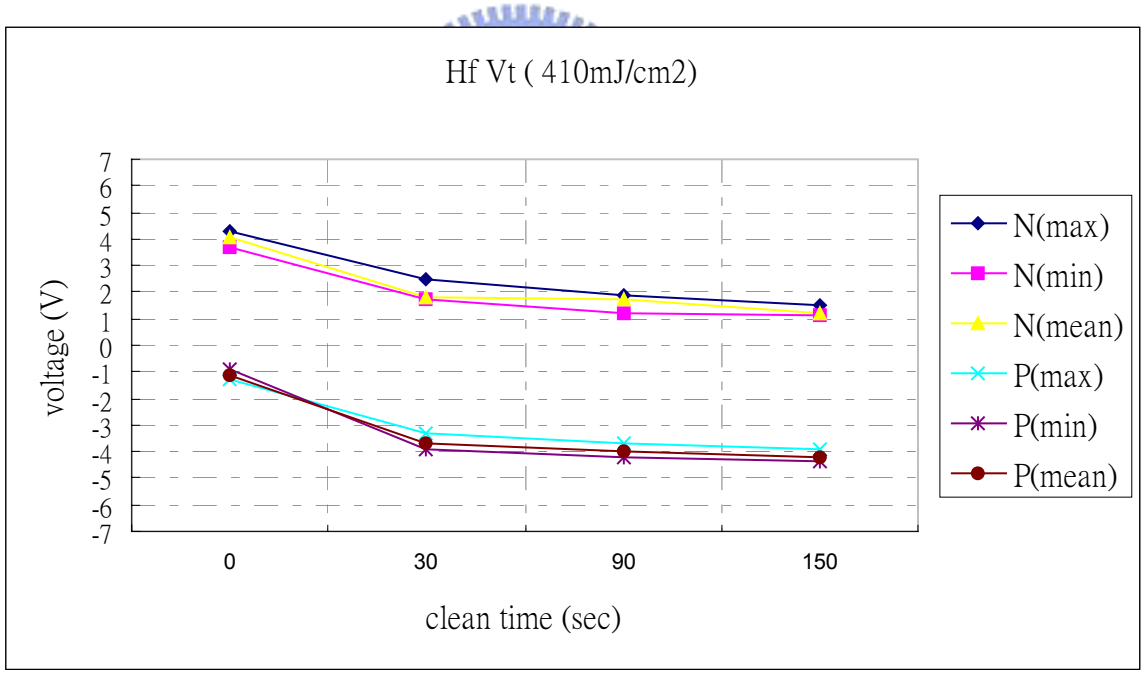

Fig. 2-53 The thresholds voltage of base pre treatment clean of HF1% in different clean time

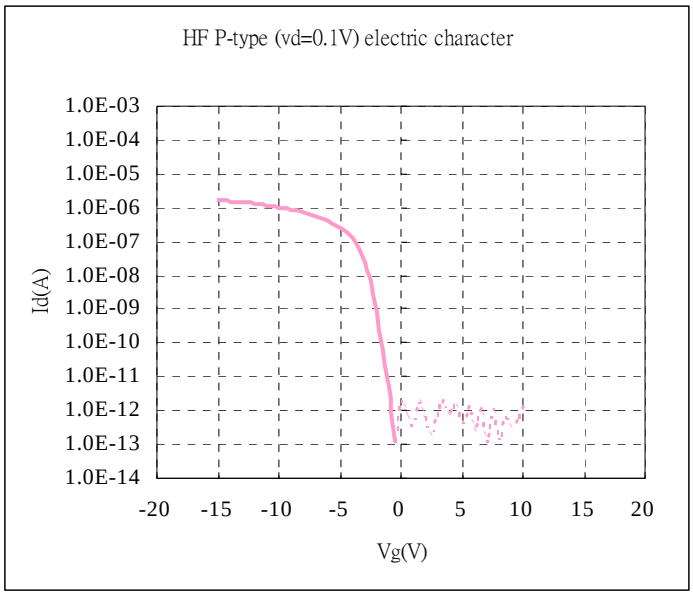

Fig. 2-54 The transfer characteristics of p type ELA poly-silicon TFTs HF1% pre clean for 30 sec, laser energy density 410mJ/cm², W/L = 6μm/12μm, Vt –3.4 V, Ufe 90 cm²/V•sec, Ioff 1.87E-13A, SS 0.45 and on/off current ratio 8.9E+6

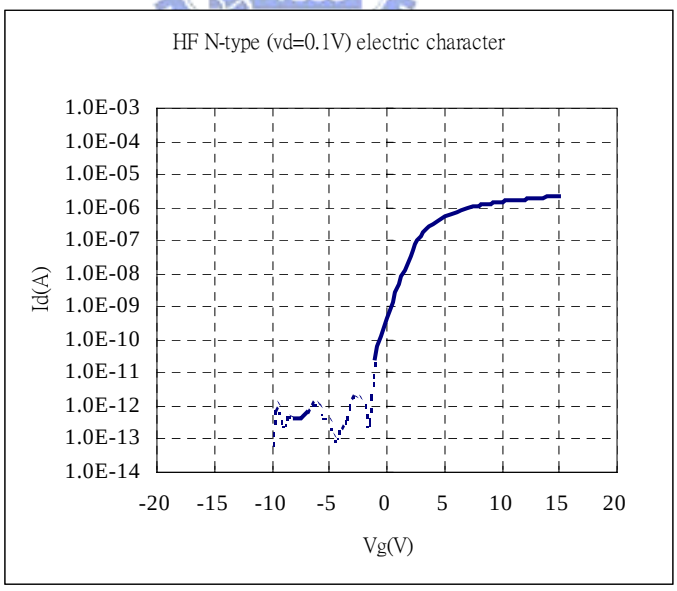

Fig. 2-55 The transfer characteristics of n type ELA poly-silicon TFTs HF1% pre clean for 30 sec, laser energy density 410mJ/cm², W/L = 6μm/12μm,Vt 2.5 V, Ufe 126 cm²/V•sec, Ioff 1.00E-14A, SS 0.71 and on/off current ratio 2.2E+8

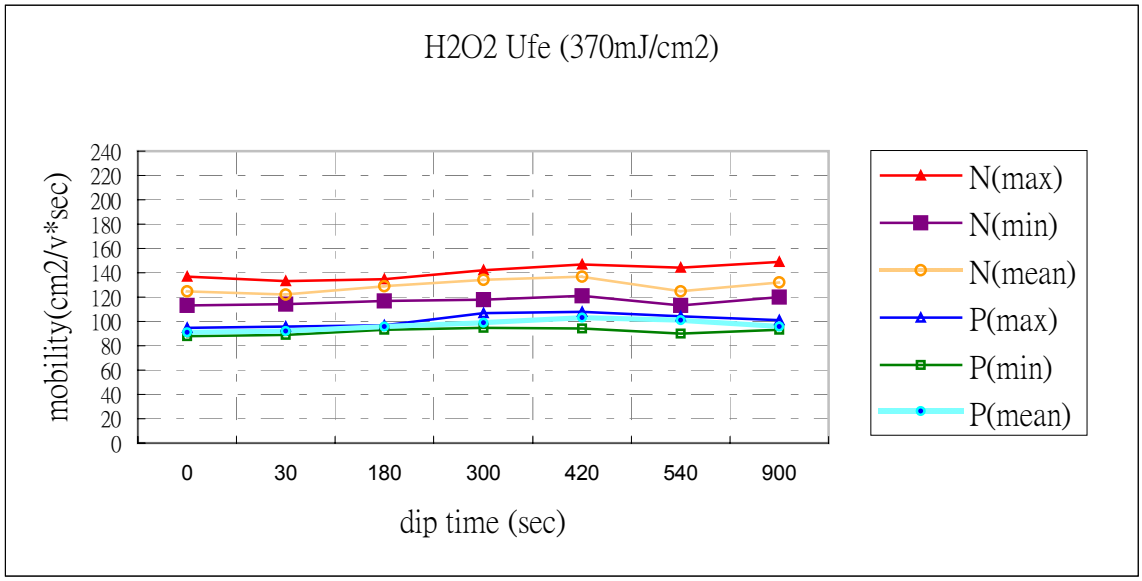

Fig. 2-56 The mobility of pre treatment clean of H2O2 30% in different clean time

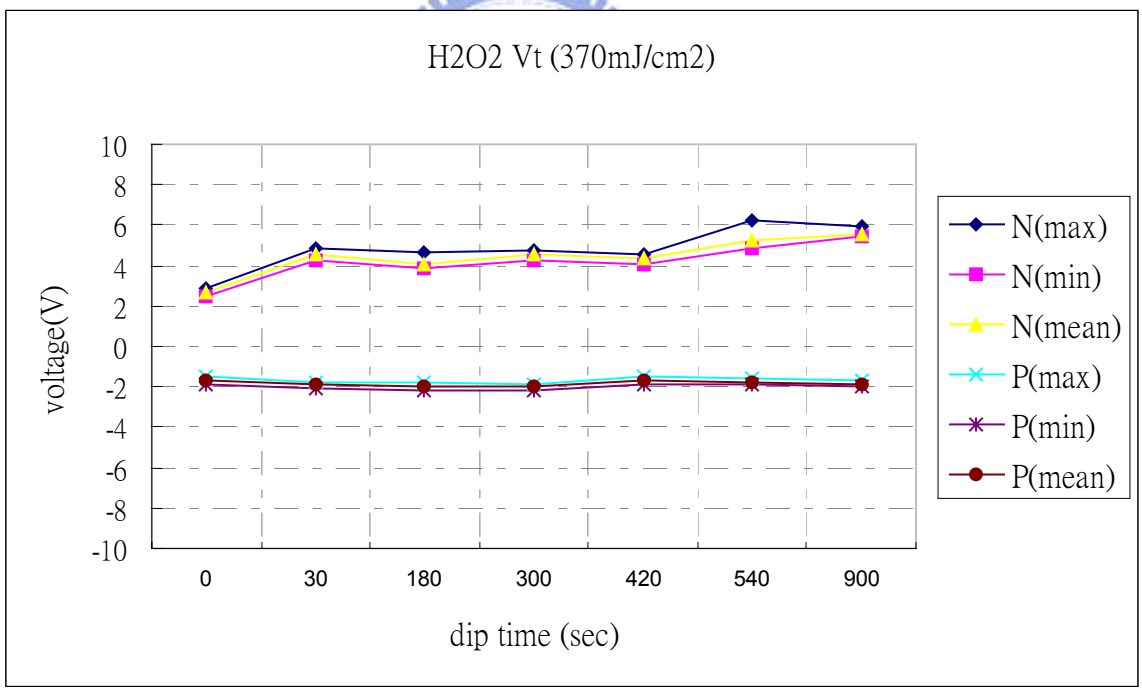

Fig. 2-57 The thresholds voltage of pre treatment clean of H2O2 30% in different clean time

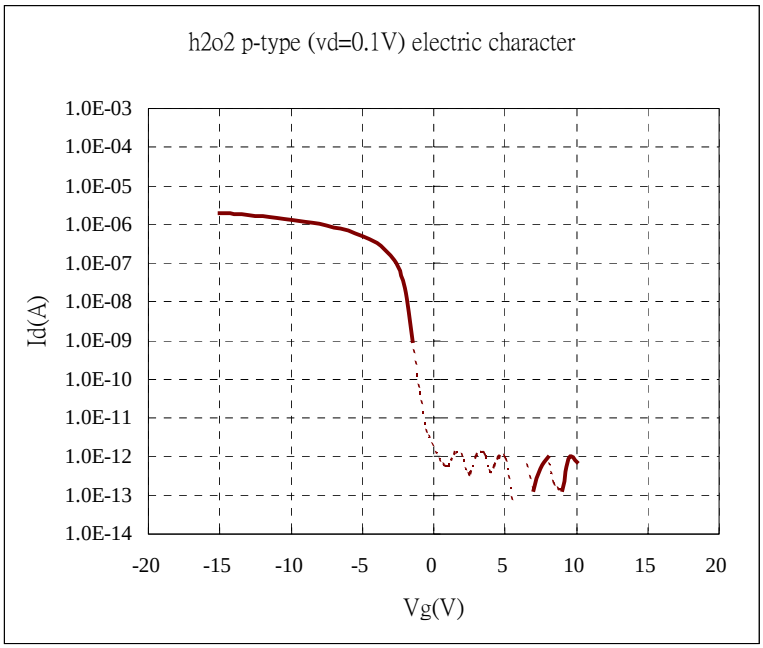

Fig. 2-58 The transfer characteristics of p type ELA poly-silicon TFTs. H2O2 pre clean for 420 sec, laser energy density 400mJ/cm², W/L = 6μm/12μm, Vt –2.2V, Ufe 104 cm²/V•sec, Ioff 1.20E-13A, SS 0.37 and on/off current ratio 1.7E+7

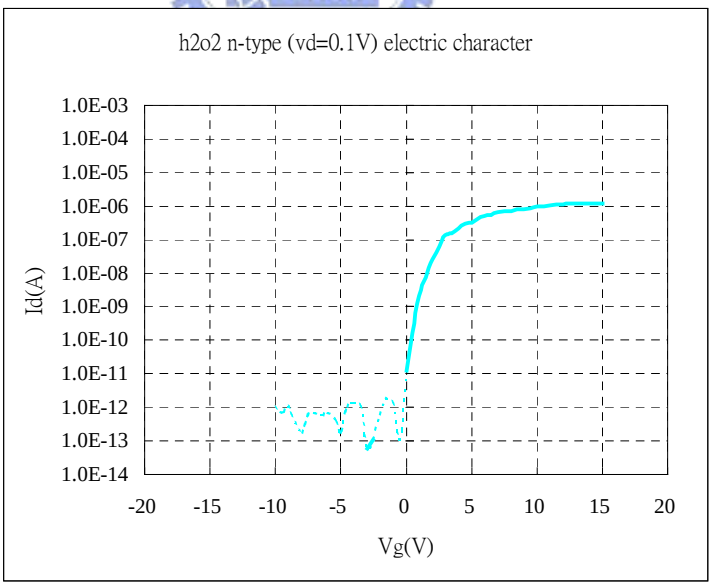

Fig. 2-59 The transfer characteristics of n type ELA poly-silicon TFTs H202 pre clean for 420 sec, laser energy density 400mJ/cm², W/L = 6μm/12μm,Vt 4.2V, Ufe 135cm²/V•sec, Ioff 1.53E-13A, SS 0.44 and on/off current ratio 8.0E+6

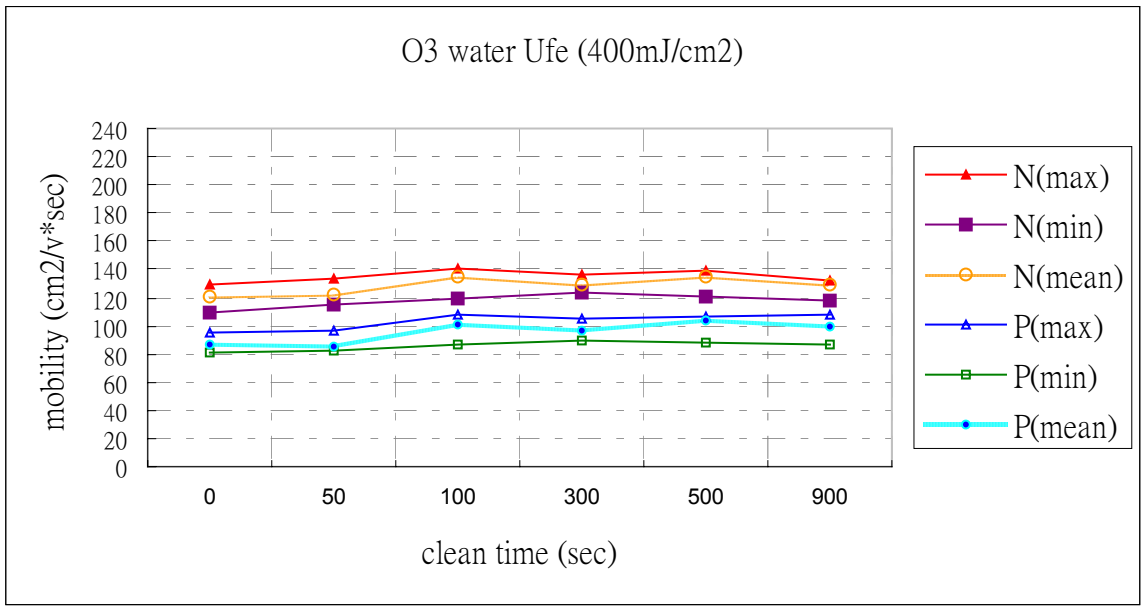

Fig. 2-60 The mobility of pre treatment clean of O3 20ppm in different clean time

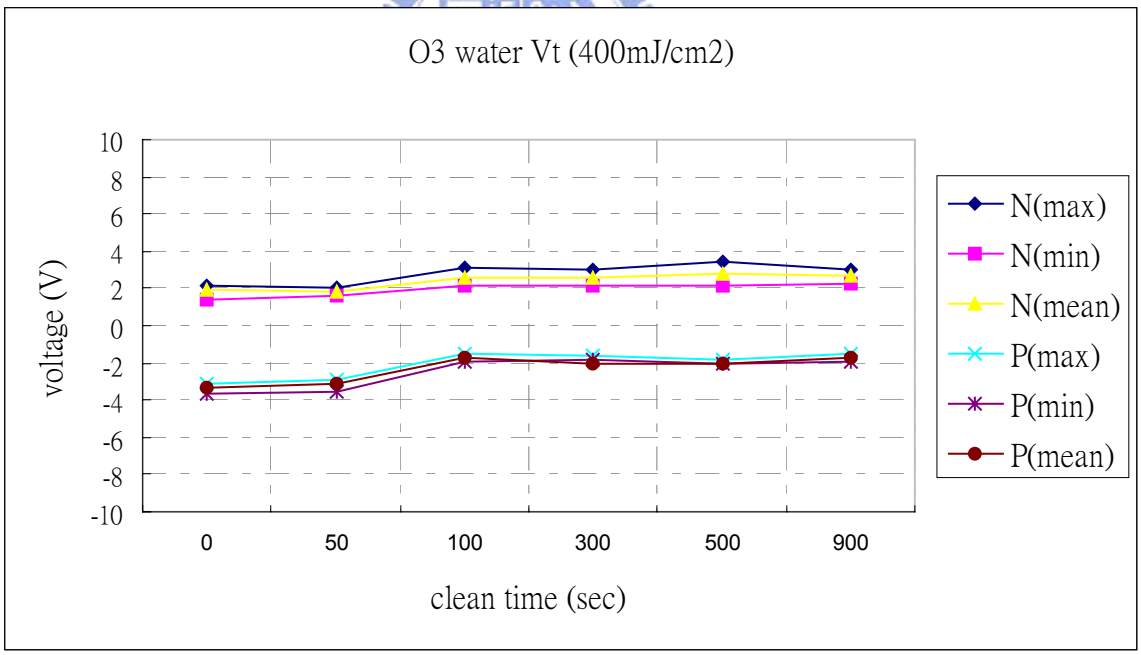

Fig. 2-61 The thresholds voltage of pre treatment clean of O3 20ppm in different clean time

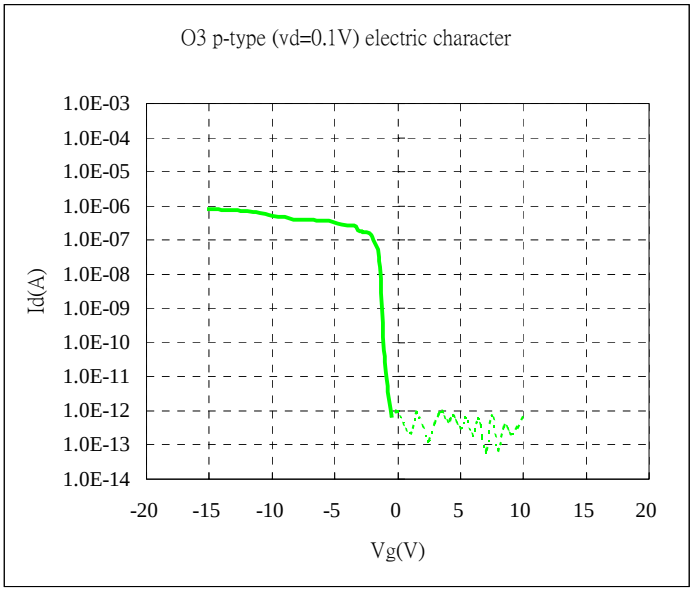

Fig. 2-62 The transfer characteristics of p type ELA poly-silicon TFTs. O3 pre clean for 100 sec, laser energy density 400mJ/cm², W/L = 6μm/12μm, Vt –1.9 V, Ufe 88 cm²/V•sec, Ioff 1.03E-13A, SS 0.16 and on/off current ratio 7.4E+6

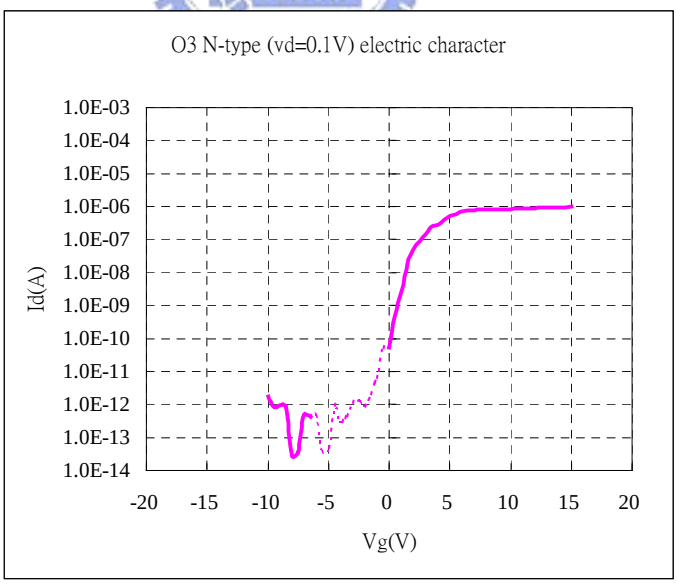

Fig. 2-63 The transfer characteristics of n type ELA poly-silicon TFTs H202 pre clean for 420 sec, laser energy density 400mJ/cm², W/L = 6μm/12μm,Vt 2.9 V, Ufe 134 cm²/V•sec, Ioff 2.87E-13A, SS 0.52 and on/off current ratio 3.4E+6

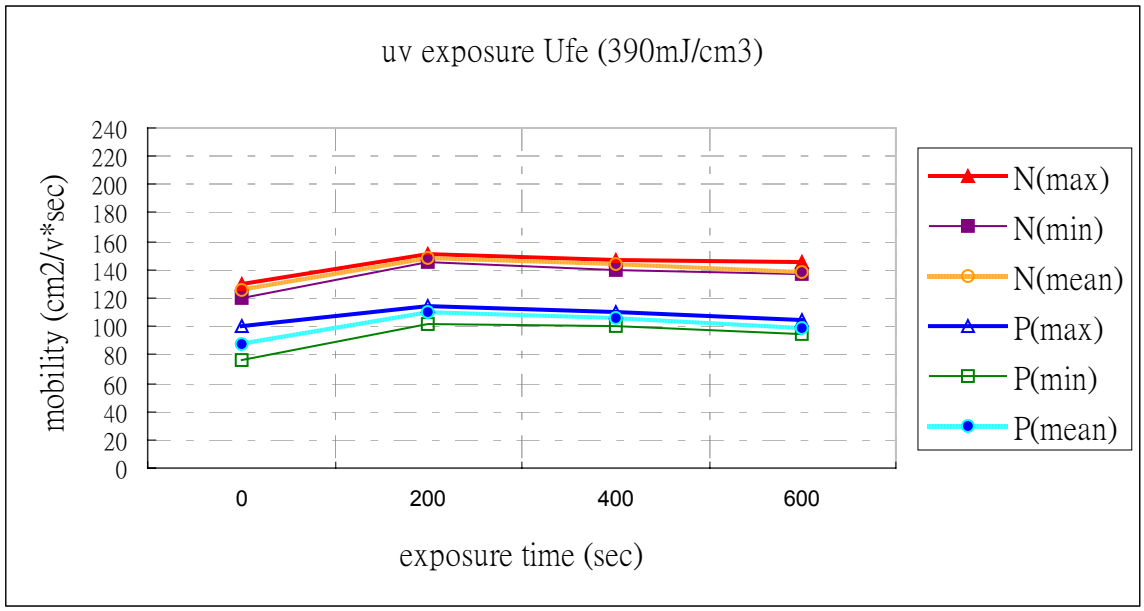

Fig. 2-64 The mobility of pre treatment clean of UV exposure λ 254nm in different clean time

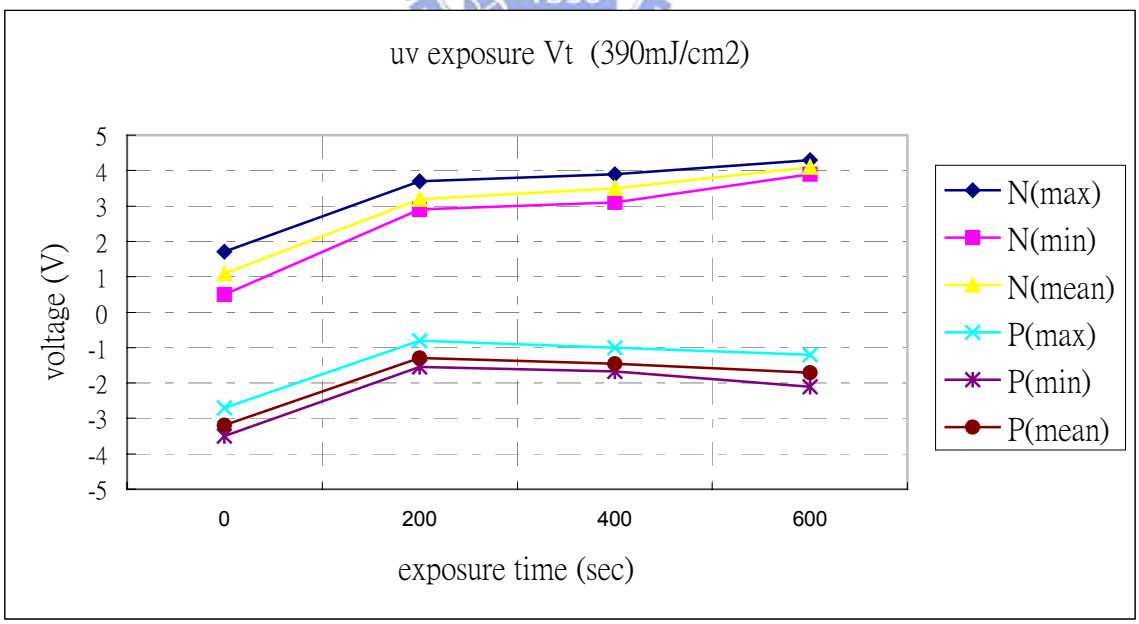

Fig. 2-65 The thresholds voltage of pre treatment clean of UV exposure λ 254nm in different clean time

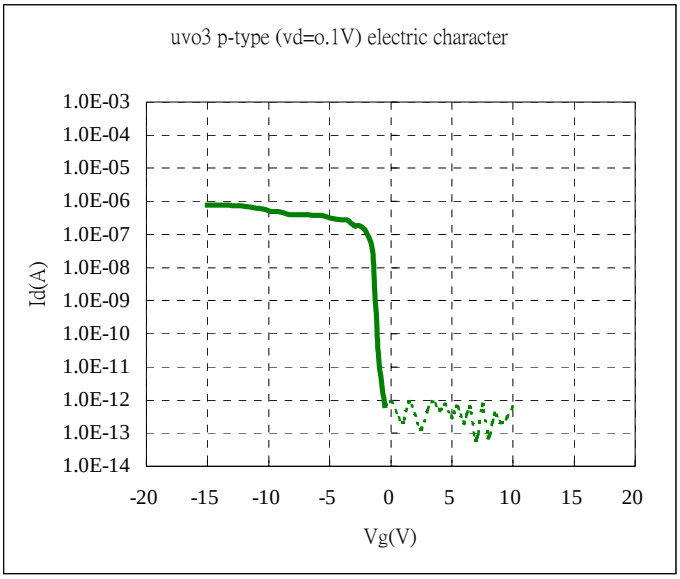

Fig. 2-66 The transfer characteristics of p type ELA poly-Silicon TFTs. UV exposure pre clean for 200 sec, laser energy density 400mJ/cm², W/L = 6μm/12μm, Vt –1.3 V, Ufe 102 cm²/V•sec, Ioff 1.07E-13A, SS 0.16 and on/off current ratio 7.3E+6

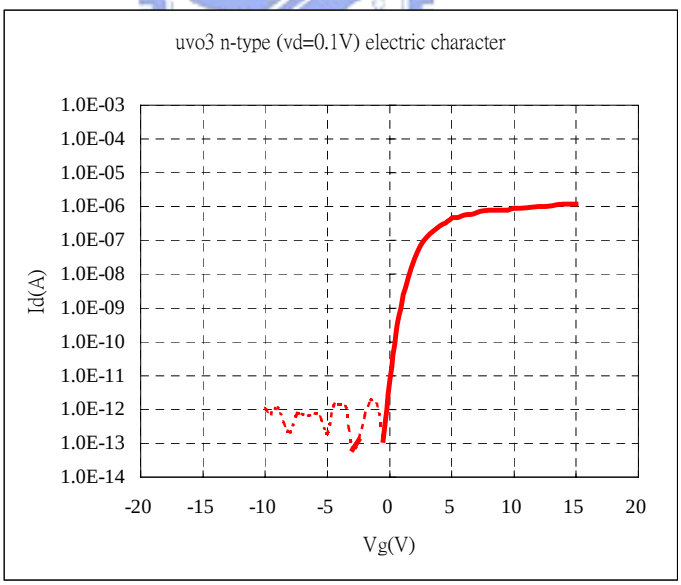

Fig. 2-67 The transfer characteristics of n type ELA poly-Silicon TFTs. UV exposure pre clean for 200 sec, laser energy density 400mJ/cm², W/L = 6μm/12μm,Vt 3.2 V, Ufe 147 cm²/V•sec, Ioff 1.71E-13A, SS 0.36 and on/off current ratio 7.0E+6